

NXP BUK9640-100A FET datasheet

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Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

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BUK9640-100A

N-channel TrenchMOS logic level FET

13 March 2014

Product data sheet

1. General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

2. Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

3. Applications

- 12 V, 24 V and 42 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	100	V
I_D	drain current	$V_{GS} = 5\text{ V}; T_{mb} = 25\text{ °C};$ Fig. 2 ; Fig. 3	-	-	39	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C};$ Fig. 1	-	-	158	W
Static characteristics						
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ °C}$	-	-	43	m Ω
		$V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ °C}$	-	29	39	m Ω
		$V_{GS} = 5\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ °C};$ Fig. 11 ; Fig. 12	-	34	40	m Ω
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 5\text{ V}; I_D = 25\text{ A}; V_{DS} = 80\text{ V};$ $T_j = 25\text{ °C};$ Fig. 13	-	20	-	nC



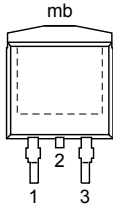
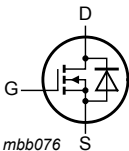
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Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 39\text{ A}$; $V_{sup} \leq 100\text{ V}$; $R_{GS} = 50\ \Omega$; $V_{GS} = 5\text{ V}$; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$; unclamped	-	-	182	mJ

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p>D2PAK (SOT404)</p>	
2	D	drain ^[1]		
3	S	source		
mb	D	mounting base; connected to drain		

[1] It is not possible to make a connection to pin 2.

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK9640-100A	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9640-100A	BUK9640-100A

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ }^\circ\text{C}$; $T_j \leq 175\text{ }^\circ\text{C}$	-	100	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	100	V
V_{GS}	gate-source voltage		-15	15	V

Symbol	Parameter	Conditions	Min	Max	Unit
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; Fig. 1	-	158	W
I_D	drain current	$T_{mb} = 25\text{ °C}$; $V_{GS} = 5\text{ V}$; Fig. 2; Fig. 3	-	39	A
		$T_{mb} = 100\text{ °C}$; $V_{GS} = 5\text{ V}$; Fig. 2	-	28	A
I_{DM}	peak drain current	$T_{mb} = 25\text{ °C}$; pulsed; $t_p \leq 10\text{ }\mu\text{s}$; Fig. 3	-	159	A
T_{stg}	storage temperature		-55	175	°C
T_j	junction temperature		-55	175	°C
Source-drain diode					
I_S	source current	$T_{mb} = 25\text{ °C}$	-	39	A
I_{SM}	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$	-	159	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 39\text{ A}$; $V_{sup} \leq 100\text{ V}$; $R_{GS} = 50\text{ }\Omega$; $V_{GS} = 5\text{ V}$; $T_{j(init)} = 25\text{ °C}$; unclamped	-	182	mJ

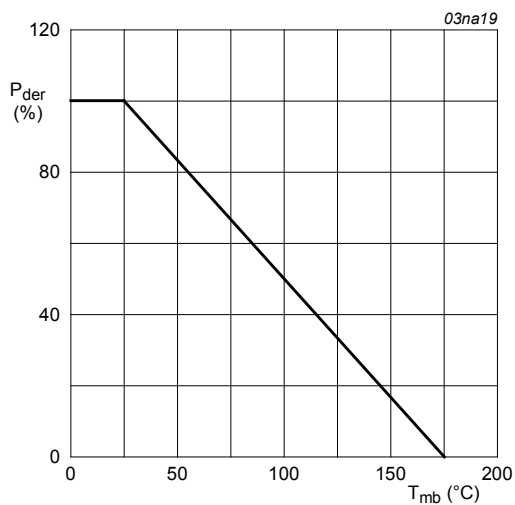


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100\%$$

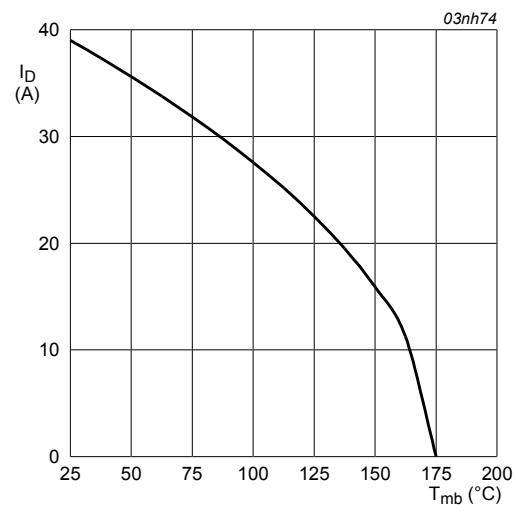


Fig. 2. Normalized continuous drain current as a function of mounting base temperature

$$T_{amb} = 25\text{ °C}; I_{DM} \text{ is single pulse}$$

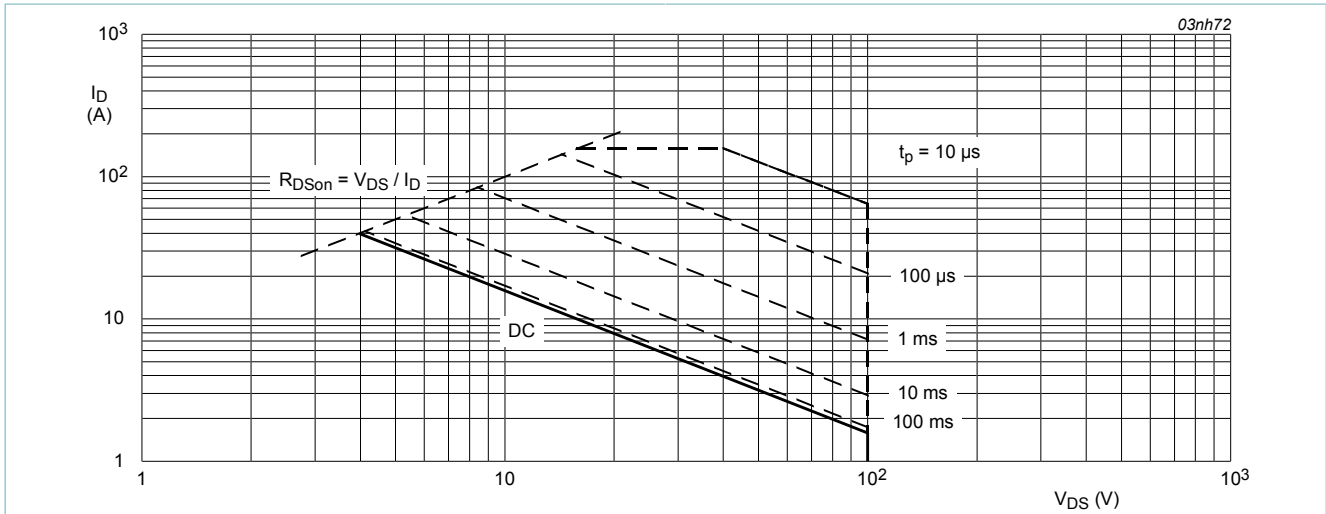


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{amb} = 25^{\circ}C; I_{DM}$ is single pulse

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 4	-	-	0.95	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	mounted on a printed-circuit board; minimum footprint	-	50	-	K/W

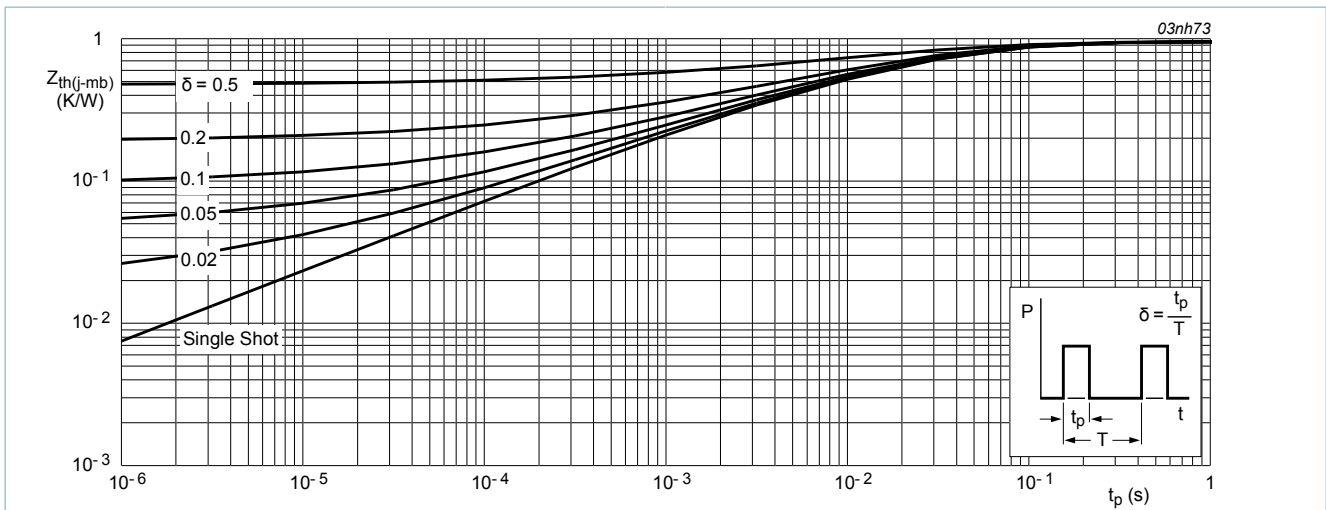


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	100	-	-	V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	89	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ Fig. 10	1	1.5	2	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$ Fig. 10	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ Fig. 10	-	-	2.3	V
I_{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ\text{C}$	-	-	500	μA
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.05	10	μA
I_{GSS}	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
		$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$	-	-	43	m Ω
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ }^\circ\text{C};$ Fig. 11; Fig. 12	-	-	100	m Ω
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$	-	29	39	m Ω
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ Fig. 11; Fig. 12	-	34	40	m Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 5 \text{ V};$ $T_j = 25 \text{ }^\circ\text{C};$ Fig. 13	-	48	-	nC
Q_{GS}	gate-source charge		-	5.4	-	nC
Q_{GD}	gate-drain charge		-	20	-	nC
C_{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^\circ\text{C};$ Fig. 14	-	2304	3072	pF
C_{oss}	output capacitance		-	222	266	pF
C_{rss}	reverse transfer capacitance		-	151	207	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \text{ } \Omega; V_{GS} = 5 \text{ V};$ $R_{G(ext)} = 10 \text{ } \Omega; T_j = 25 \text{ }^\circ\text{C}$	-	20	-	ns
t_r	rise time		-	135	-	ns
$t_{d(off)}$	turn-off delay time		-	125	-	ns
t_f	fall time		-	90	-	ns
L_D	internal drain inductance	from upper edge of drain mounting base to centre of die; $T_j = 25 \text{ }^\circ\text{C}$	-	2.5	-	nH

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		from drain lead 6 mm from package to centre of die; $T_j = 25\text{ }^\circ\text{C}$	-	4.5	-	nH
L_S	internal source inductance	from source lead to source bond pad; $T_j = 25\text{ }^\circ\text{C}$	-	7.5	-	nH
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 25\text{ A}$; $V_{GS} = 0\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 15	-	0.85	1.2	V
t_{rr}	reverse recovery time	$I_S = 37\text{ A}$; $dI_S/dt = -100\text{ A}/\mu\text{s}$;	-	60	-	ns
Q_r	recovered charge	$V_{GS} = -10\text{ V}$; $V_{DS} = 30\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$	-	240	-	nC

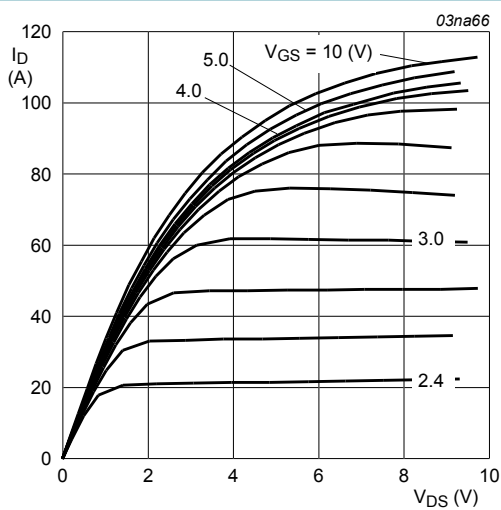


Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values

$T_j = 25\text{ }^\circ\text{C}$; $t_p = 300\mu\text{s}$

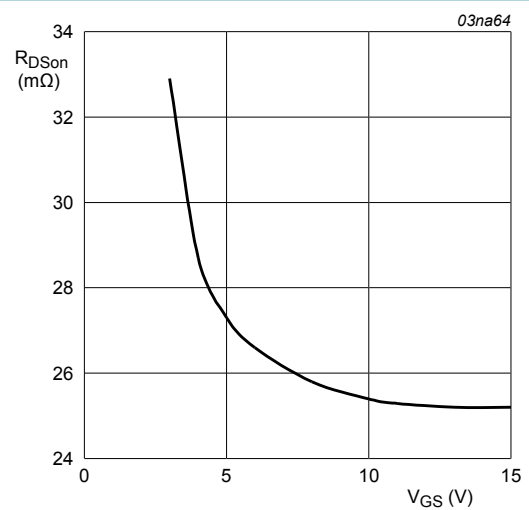
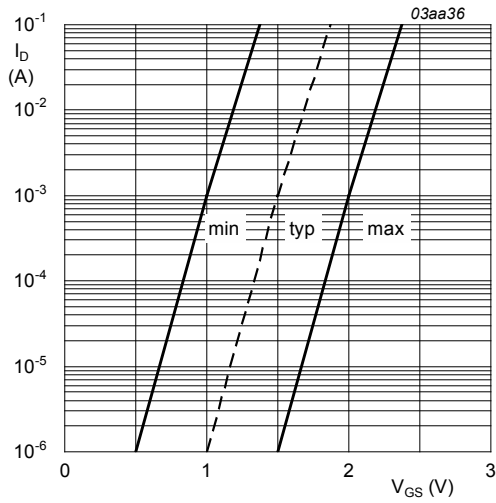


Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25\text{ }^\circ\text{C}$; $I_D = 25\text{ A}$



$T_j = 25\text{ }^\circ\text{C}; V_{DS} = 5\text{ V}$

Fig. 7. Sub-threshold drain current as a function of gate-source voltage

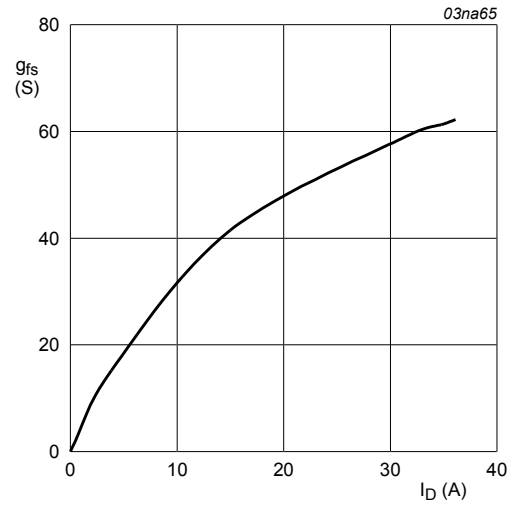


Fig. 8. Forward transconductance as a function of drain current; typical values

$T_j = 25\text{ }^\circ\text{C}; V_{DS} = 25\text{ V}$

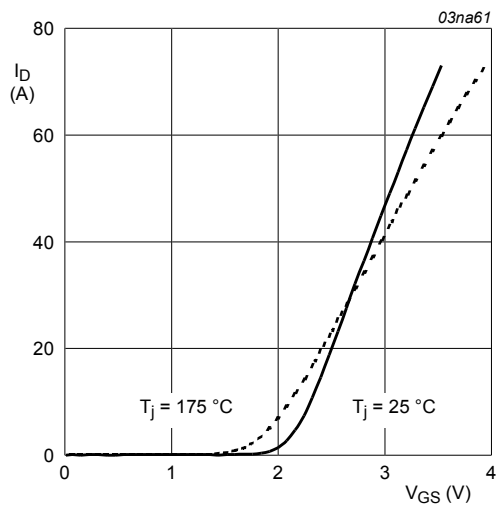


Fig. 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$V_{DS} = 25\text{ V}$

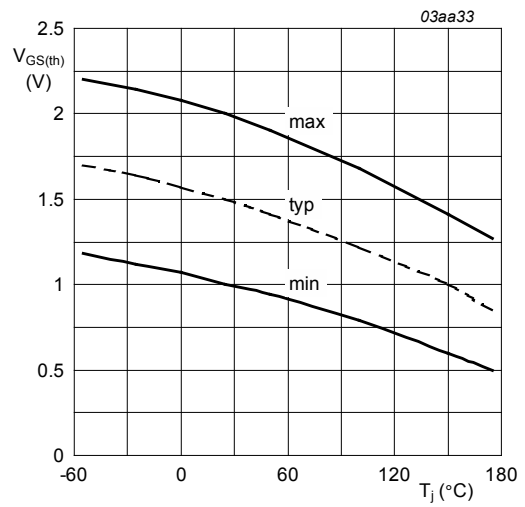


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

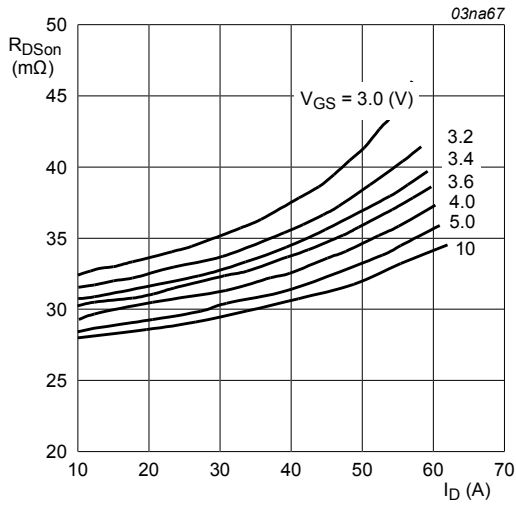


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

$T_j = 25^\circ C$

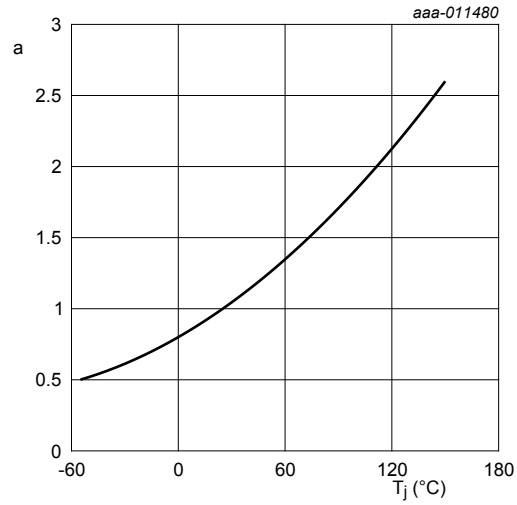


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DS(on)}}{R_{DS(on)(25^\circ C)}}$$

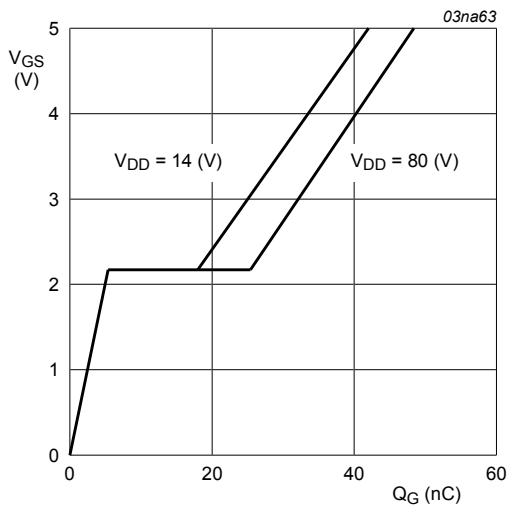


Fig. 13. Gate-source voltage as a function of gate charge; typical values

$T_j = 25^\circ C; I_D = 25A$

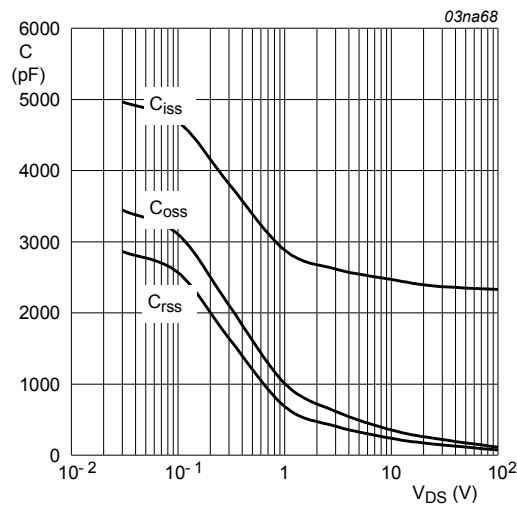


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0V; f = 1MHz$

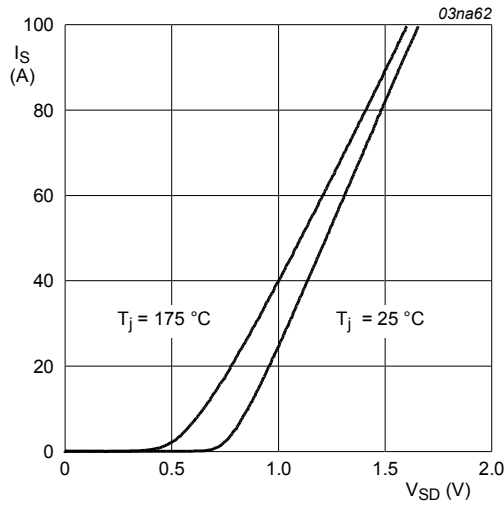


Fig. 15. Source current as a function of source-drain voltage; typical values

$$V_{GS} = 0V$$

11. Package outline

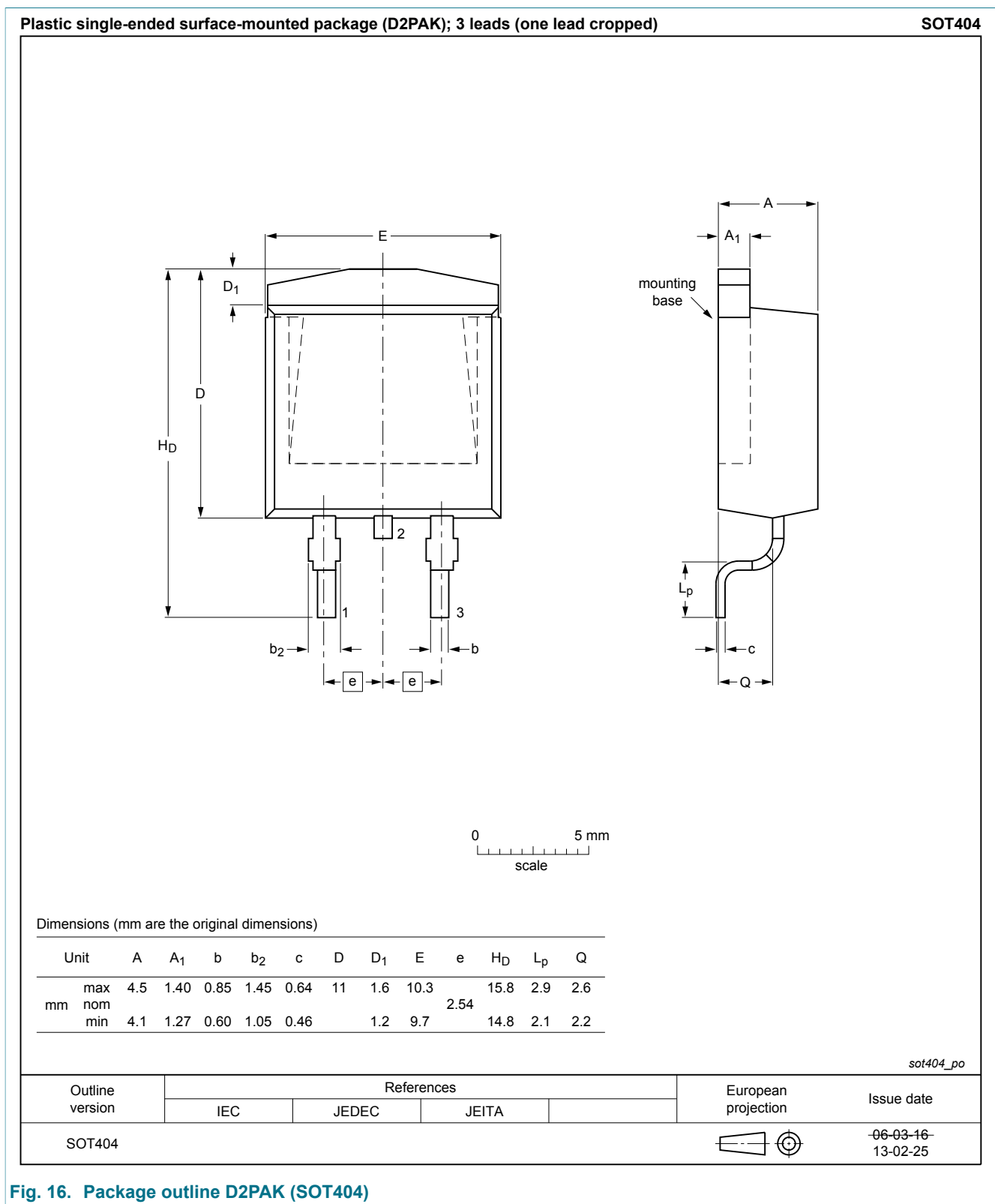


Fig. 16. Package outline D2PAK (SOT404)

12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Date of release: 13 March 2014